

< HVIGBT MODULES >

CM1200HG-90R

HIGH POWER SWITCHING USE
INSULATED TYPE

4th-Version HVIGBT (High Voltage Insulated Gate Bipolar Transistor) Modules

CM1200HG-90R



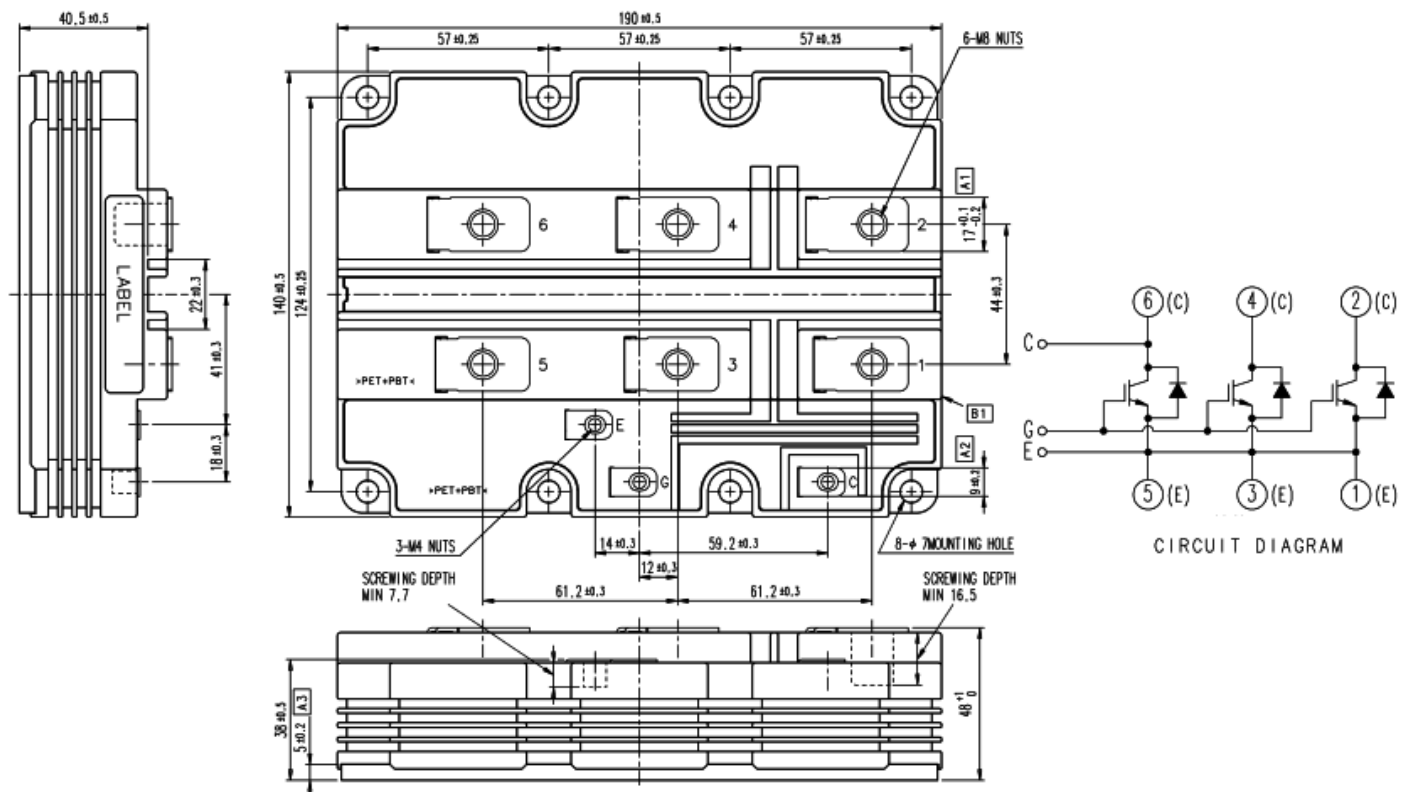
- I_C 1200A
- V_{CES} 4500V
- 1-element in a Pack
- High insulated Type
- LPT-IGBT / Soft Recovery Diode
- AISiC Baseplate

APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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MAXIMUM RATINGS

Symbol	Item	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	V _{GE} = 0V, T _J = -40...+125°C	4500	V
		V _{GE} = 0V, T _J = -50°C	4400	
V _{GES}	Gate-emitter voltage	V _{CE} = 0V, T _J = 25°C	± 20	V
I _C	Collector current	DC, T _C = 85°C	1200	A
I _{CRM}		Pulse (Note 1)	2400	A
I _E	Emitter current (Note 2)	DC	1200	A
I _{ERM}		Pulse (Note 1)	2400	A
P _{tot}	Maximum power dissipation (Note 3)	T _C = 25°C, IGBT part	11900	W
V _{iso}	Isolation voltage	RMS, sinusoidal, f = 60Hz, t = 1 min.	10200	V
V _e	Partial discharge extinction voltage	RMS, sinusoidal, f = 60Hz, Q _{PD} ≤ 10 pC	5100	V
T _J	Junction temperature		-50 ~ +150	°C
T _{Jop}	Operating junction temperature		-50 ~ +125	°C
T _{stg}	Storage temperature		-55 ~ +125	°C
t _{psc}	Short circuit pulse width	V _{CC} = 3200V, V _{CE} ≤ V _{CES} , V _{GE} = 15V, T _J = 125°C	10	μs

ELECTRICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min	Typ	Max		
I _{CES}	Collector cutoff current	V _{CE} = V _{CES} , V _{GE} = 0V	T _J = 25°C	—	—	16.0	mA
			T _J = 125°C	—	16.0	—	
V _{GE(th)}	Gate-emitter threshold voltage	V _{CE} = 10 V, I _C = 120 mA, T _J = 25°C	5.8	6.3	6.8		
I _{GES}	Gate leakage current	V _{GE} = V _{GES} , V _{CE} = 0V, T _J = 25°C	-0.5	—	0.5		
C _{ies}	Input capacitance	V _{CE} = 10 V, V _{GE} = 0 V, f = 100 kHz T _J = 25°C	—	175.0	—		
C _{oes}	Output capacitance		—	11.0	—		
C _{res}	Reverse transfer capacitance		—	5.0	—		
Q _G	Total gate charge	V _{CC} = 2800V, I _C = 1200A, V _{GE} = ±15V	—	13.5	—		
V _{CEsat}	Collector-emitter saturation voltage	I _C = 1200 A (Note 4) V _{GE} = 15 V	T _J = 25°C	—	3.50	—	V
			T _J = 125°C	—	4.40	5.20	
t _{d(on)}	Turn-on delay time	V _{CC} = 2800 V I _C = 1200 A	T _J = 25°C	—	1.00	—	μs
			T _J = 125°C	—	0.95	1.50	
t _r	Turn-on rise time	V _{GE} = ±15 V	T _J = 25°C	—	0.28	—	μs
			T _J = 125°C	—	0.30	0.50	
E _{on(10%)}	Turn-on switching energy (Note 5)	R _{G(on)} = 2.7 Ω L _S = 150 nH	T _J = 25°C	—	3.90	—	J
			T _J = 125°C	—	4.70	—	
E _{on}	Turn-on switching energy (Note 6)	Inductive load	T _J = 25°C	—	4.20	—	J
			T _J = 125°C	—	5.50	—	
t _{d(off)}	Turn-off delay time	V _{CC} = 2800 V I _C = 1200 A	T _J = 25°C	—	3.60	—	μs
			T _J = 125°C	—	3.80	5.00	
t _f	Turn-off fall time	V _{GE} = ±15 V	T _J = 25°C	—	0.35	—	μs
			T _J = 125°C	—	0.45	1.00	
E _{off(10%)}	Turn-off switching energy (Note 5)	R _{G(off)} = 10 Ω L _S = 150 nH	T _J = 25°C	—	2.90	—	J
			T _J = 125°C	—	3.85	—	
E _{off}	Turn-off switching energy (Note 6)	Inductive load	T _J = 25°C	—	3.20	—	J
			T _J = 125°C	—	4.30	—	

ELECTRICAL CHARACTERISTICS (continuation)

Symbol	Item	Conditions	Limits			Unit	
			Min	Typ	Max		
V_{EC}	Emitter-collector voltage (Note 2)	$I_E = 1200 \text{ A}$ (Note 4) $V_{GE} = 0 \text{ V}$	$T_j = 25^\circ\text{C}$	—	2.60	—	V
			$T_j = 125^\circ\text{C}$	—	2.80	3.40	
t_{rr}	Reverse recovery time (Note 2)	$V_{CC} = 2800 \text{ V}$ $I_C = 1200 \text{ A}$ $V_{GE} = \pm 15 \text{ V}$ $R_{G(on)} = 2.7 \Omega$ $L_s = 150 \text{ nH}$ Inductive load	$T_j = 25^\circ\text{C}$	—	0.70	—	μs
			$T_j = 125^\circ\text{C}$	—	0.90	—	
I_{rr}	Reverse recovery current (Note 2)	$V_{CC} = 2800 \text{ V}$ $I_C = 1200 \text{ A}$ $V_{GE} = \pm 15 \text{ V}$ $R_{G(on)} = 2.7 \Omega$ $L_s = 150 \text{ nH}$ Inductive load	$T_j = 25^\circ\text{C}$	—	1200	—	A
			$T_j = 125^\circ\text{C}$	—	1300	—	
Q_{rr}	Reverse recovery charge (Note 2)	$V_{CC} = 2800 \text{ V}$ $I_C = 1200 \text{ A}$ $V_{GE} = \pm 15 \text{ V}$ $R_{G(on)} = 2.7 \Omega$ $L_s = 150 \text{ nH}$ Inductive load	$T_j = 25^\circ\text{C}$	—	1100	—	μC
			$T_j = 125^\circ\text{C}$	—	1700	—	
$E_{rec(10\%)}$	Reverse recovery energy (Note 2) (Note 5)	$V_{CC} = 2800 \text{ V}$ $I_C = 1200 \text{ A}$ $V_{GE} = \pm 15 \text{ V}$ $R_{G(on)} = 2.7 \Omega$ $L_s = 150 \text{ nH}$ Inductive load	$T_j = 25^\circ\text{C}$	—	1.40	—	J
			$T_j = 125^\circ\text{C}$	—	2.25	—	
E_{rec}	Reverse recovery energy (Note 2) (Note 6)	$V_{CC} = 2800 \text{ V}$ $I_C = 1200 \text{ A}$ $V_{GE} = \pm 15 \text{ V}$ $R_{G(on)} = 2.7 \Omega$ $L_s = 150 \text{ nH}$ Inductive load	$T_j = 25^\circ\text{C}$	—	1.60	—	J
			$T_j = 125^\circ\text{C}$	—	2.50	—	

THERMAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
$R_{th(j-c)Q}$	Thermal resistance	Junction to Case, IGBT part	—	—	10.5	K/kW
$R_{th(j-c)D}$		Junction to Case, FWDi part	—	—	19.5	
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, $\lambda_{grease} = 1\text{W/m}^2\text{K}$, $D_{(c-s)} = 100\mu\text{m}$	—	6.0	—	K/kW

MECHANICAL CHARACTERISTICS

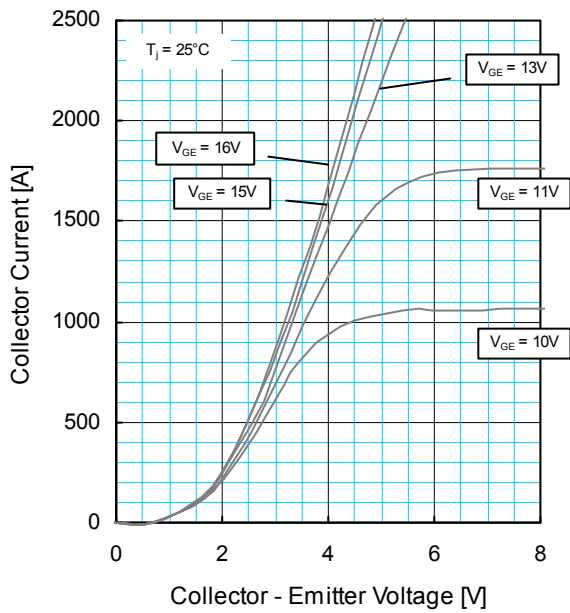
Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
M_t	Mounting torque	M : Main terminals screw	7.0	—	22.0	N·m
M_s		M : Mounting screw	3.0	—	6.0	
M_t		M : Auxiliary terminals screw	1.0	—	3.0	
m	Mass		—	1.4	—	kg
CTI	Comparative tracking index		600	—	—	—
d_a	Clearance		26.0	—	—	mm
d_s	Creepage distance		56.0	—	—	mm
L_{PCE}	Parasitic stray inductance		—	15.0	—	nH
R_{CC+EE}	Internal lead resistance	$T_c = 25^\circ\text{C}$	—	0.18	—	$\text{M}\Omega$
r_g	Internal gate resistance	$T_c = 25^\circ\text{C}$	—	1.7	—	Ω

Note1. Pulse width and repetition rate should be such that junction temperature (T_j) does not exceed Topmax rating.

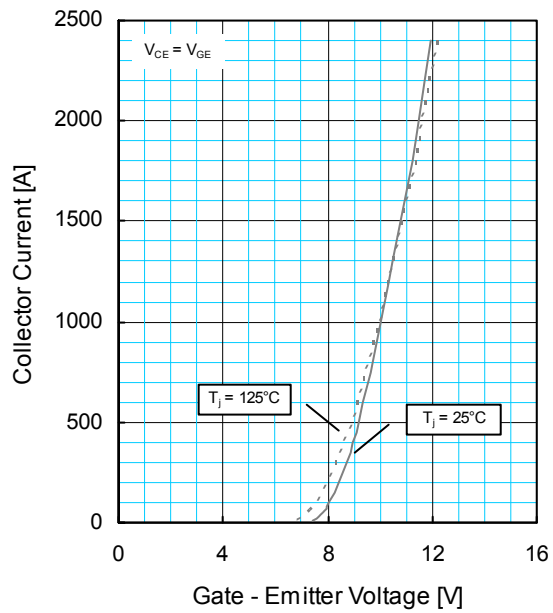
- The symbols represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWD).
- Junction temperature (T_j) should not exceed T_{jmax} rating (150°C).
- Pulse width and repetition rate should be such as to cause negligible temperature rise.
- $E_{on(10\%)} / E_{off(10\%)} / E_{rec(10\%)}$ are the integral of $0.1V_{CE} \times 0.1I_C \times dt$.
- Definition of all items is according to IEC 60747, unless otherwise specified.

PERFORMANCE CURVES

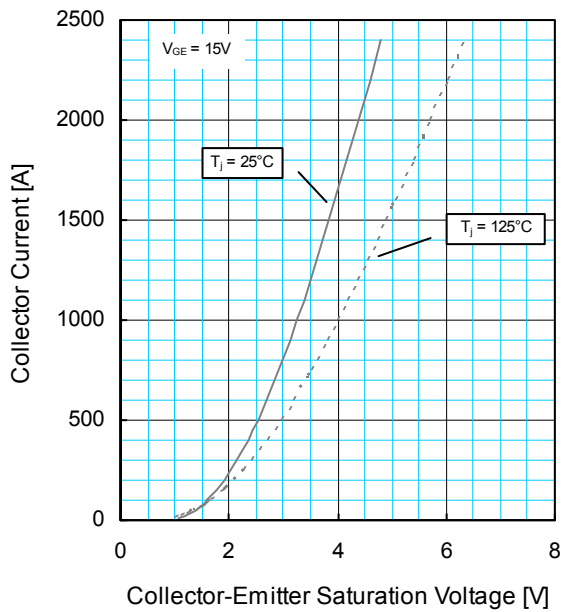
OUTPUT CHARACTERISTICS (TYPICAL)



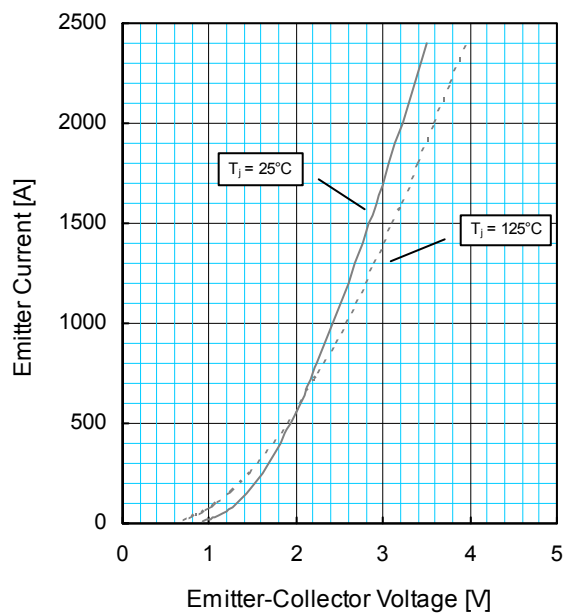
TRANSFER CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)

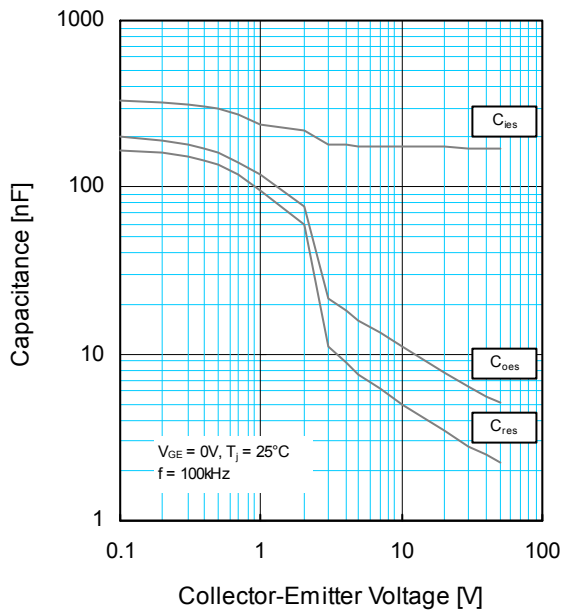


FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)

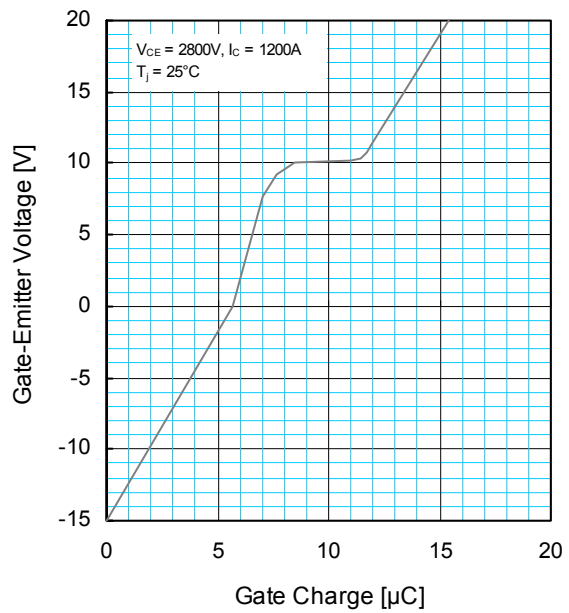


PERFORMANCE CURVES

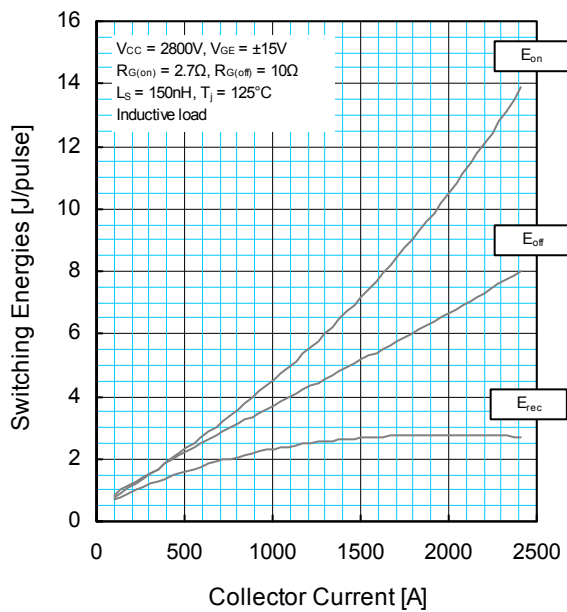
CAPACITANCE CHARACTERISTICS (TYPICAL)



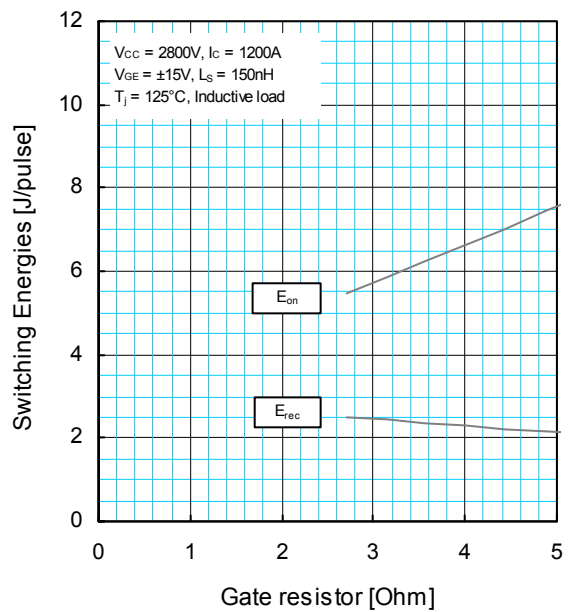
GATE CHARGE CHARACTERISTICS (TYPICAL)



HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)

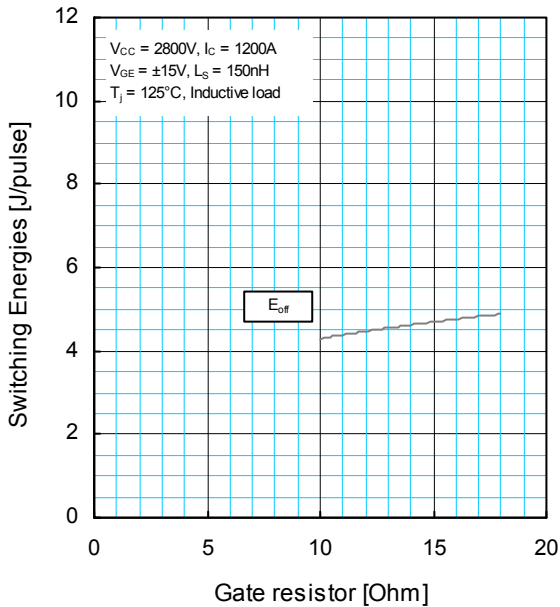


HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)

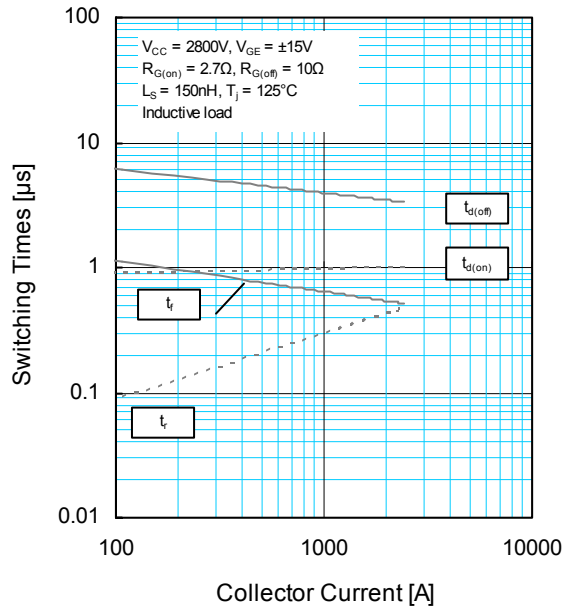


PERFORMANCE CURVES

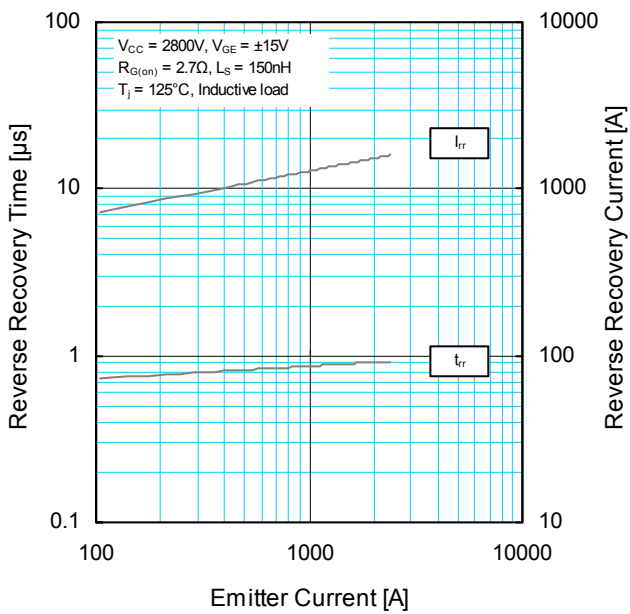
HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



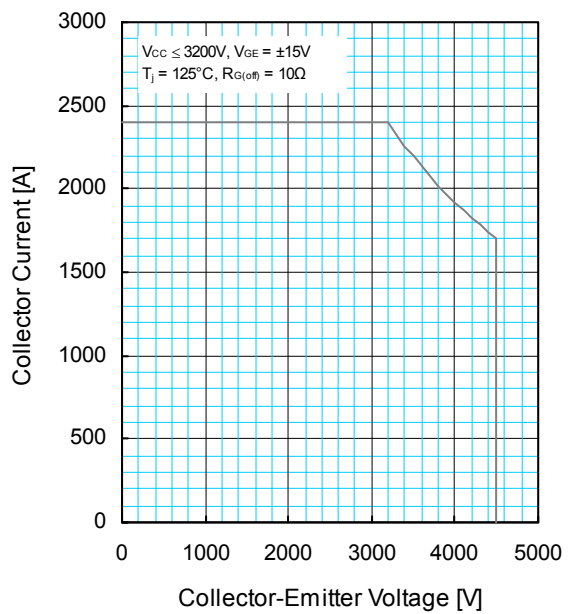
HALF-BRIDGE SWITCHING TIME CHARACTERISTICS (TYPICAL)



FREE-WHEEL DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

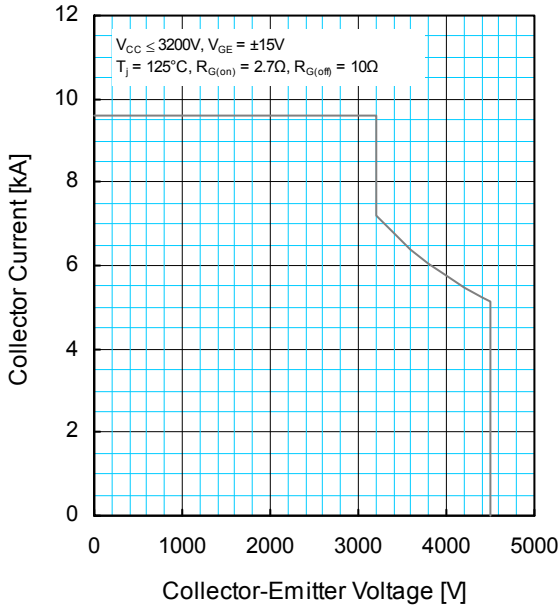


REVERSE BIAS SAFE OPERATING AREA (RBSOA)

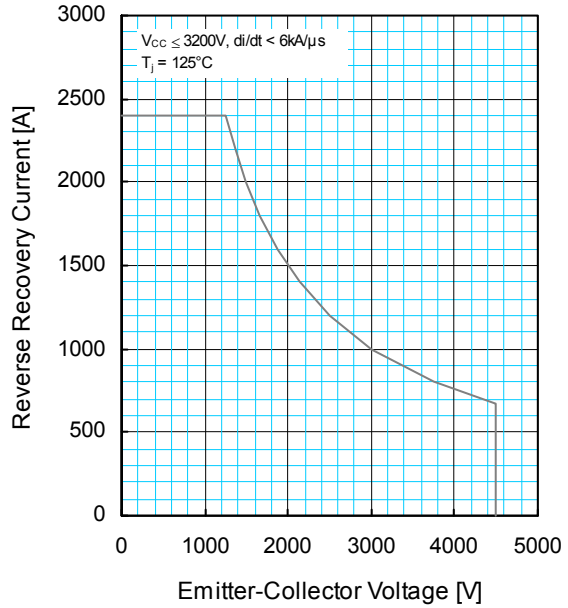


PERFORMANCE CURVES

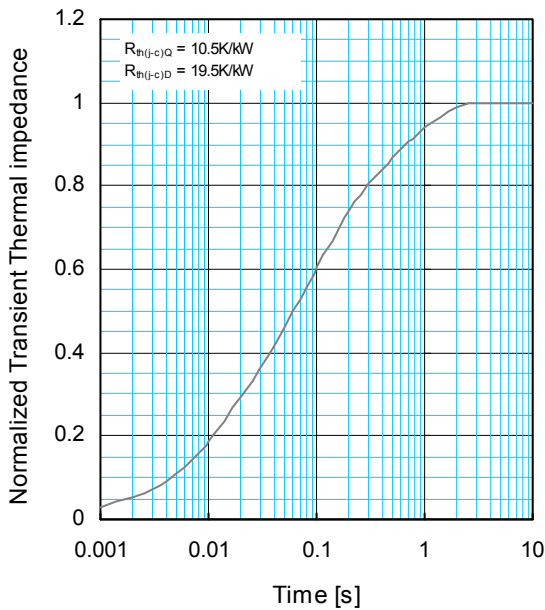
**SHORT CIRCUIT
SAFE OPERATING AREA (SCSOA)**



**FREE-WHEEL DIODE REVERSE RECOVERY
SAFE OPERATING AREA (RRSOA)**



**TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS**



$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i \left\{ 1 - \exp\left(-\frac{t}{\tau_i}\right) \right\}$$

	1	2	3	4
R_i [K/kW] :	0.0055	0.2360	0.4680	0.2905
τ_i [sec] :	0.0001	0.0131	0.0878	0.6247

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